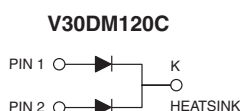
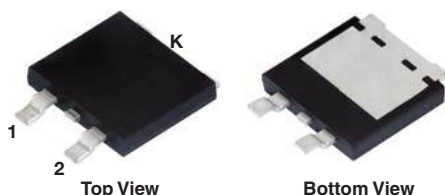


## Dual Trench MOS Barrier Schottky Rectifier

Ultra Low  $V_F = 0.51\text{ V}$  at  $I_F = 5\text{ A}$

**TMBS® eSMP® Series**  
**TO-263AC (SMPD)**



### FEATURES

- Trench MOS Schottky technology
- Very low profile - typical height of 1.7 mm
- Ideal for automated placement
- Low forward voltage drop, low power losses
- High efficiency operation
- AEC-Q101 qualified available:
  - Automotive ordering code: base P/NHM3
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?999912](http://www.vishay.com/doc?999912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### TYPICAL APPLICATIONS

For use in high frequency DC/DC converters, switching power supplies, freewheeling diodes, OR-ing diode, and reverse battery protection in commercial, industrial, and automotive application.

### MECHANICAL DATA

**Case:** TO-263AC SMPD

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

Base P/NHM3 - halogen-free, RoHS-compliant, and

AEC-Q101 qualified

**Terminals:** Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

M3 and HM3 suffix meets JESD 201 class 2 whisker test

**Polarity:** As marked

| PRIMARY CHARACTERISTICS                                |                     |
|--|---------------------|
| $I_{F(AV)}$  | 2 x 15 A            |
| $V_{RRM}$  | 120 V               |
| $I_{FSM}$  | 150 A               |
| $V_F$ at $I_F = 15\text{ A}$ ( $T_A = 125\text{ °C}$ ) | 0.67 V              |
| $T_J$ max.   | 175 °C              |
| Package  | TO-263AC (SMPD)     |
| Diode variations                                       | Dual common cathode |

| MAXIMUM RATINGS ( $T_A = 25\text{ °C}$ unless otherwise noted)                    |                |             |            |
|---|----------------|-------------|------------|
| PARAMETER   | SYMBOL         | V30DM120C   | UNIT       |
| Maximum repetitive peak reverse voltage   | $V_{RRM}$      | 120         | V          |
| Maximum average forward rectified current<br>(fig. 1)                             | $I_{F(AV)}$    | 30          | A          |
|   |                | 15          |            |
| Peak forward surge current 10 ms single half sine-wave superimposed on rated load | $I_{FSM}$      | 150         | A          |
| Voltage rate of change (rated $V_R$ )   | $dV/dt$        | 10 000      | V/ $\mu$ s |
| Operating junction and storage temperature range                                  | $T_J, T_{STG}$ | -40 to +175 | °C         |

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25\text{ }^{\circ}\text{C}$  unless otherwise noted)

| PARAMETER                               | TEST CONDITIONS      | SYMBOL                              | TYP. | MAX. | UNIT          |
|---|----------------------|-------------------------------------|------|------|---------------|
| Instantaneous forward voltage per diode | $I_F = 5\text{ A}$   | $V_F^{(1)}$                         | 0.59 | -    | V             |
|   | $I_F = 7.5\text{ A}$ |                                     | 0.66 | -    |               |
|   | $I_F = 15\text{ A}$  |                                     | 0.88 | 0.97 |               |
|   | $I_F = 5\text{ A}$   | $T_A = 125\text{ }^{\circ}\text{C}$ | 0.51 | -    |               |
|   | $I_F = 7.5\text{ A}$ |                                     | 0.56 | -    |               |
|   | $I_F = 15\text{ A}$  |                                     | 0.67 | 0.76 |               |
| Reverse current per diode               | $V_R = 90\text{ V}$  | $T_A = 25\text{ }^{\circ}\text{C}$  | 5    | -    | $\mu\text{A}$ |
|   |                      | $T_A = 125\text{ }^{\circ}\text{C}$ | 3.1  | -    | mA            |
|   | $V_R = 120\text{ V}$ | $T_A = 25\text{ }^{\circ}\text{C}$  | -    | 800  | $\mu\text{A}$ |
|   |                      | $T_A = 125\text{ }^{\circ}\text{C}$ | 6    | 27   | mA            |

**Notes**(1) Pulse test: 300  $\mu\text{s}$  pulse width, 1 % duty cycle(2) Pulse test: Pulse width  $\leq 5\text{ ms}$ **THERMAL CHARACTERISTICS** ( $T_A = 25\text{ }^{\circ}\text{C}$  unless otherwise noted)

| PARAMETER                  | SYMBOL                   | V30DM120C  | UNIT |
|----------------------------|--------------------------|------------|------|
| Typical thermal resistance | $R_{\theta JC}$          | per diode  | 2.2  |
|                            |                          | per device | 1.2  |
|                            | $R_{\theta JA}^{(1)(2)}$ | per device | 48   |

**Notes**(1) The heat generated must be less than the thermal conductivity from junction-to-ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ 

(2) Free air, without heatsink

**ORDERING INFORMATION** (Example)

| PACKAGE         | PREFERRED P/N                 | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE                      |
|-----------------|-------------------------------|-----------------|--------------|---------------|------------------------------------|
| TO-263AC (SMPD) | V30DM120C-M3/I                | 0.55            | I            | 2000/reel     | 13" diameter plastic tape and reel |
| TO-263AC (SMPD) | V30DM120CHM3/I <sup>(1)</sup> | 0.55            | I            | 2000/reel     | 13" diameter plastic tape and reel |

**Note**

(1) AEC-Q101 qualified

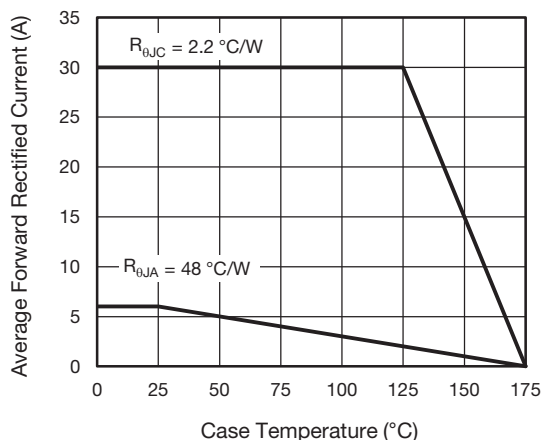
**RATINGS AND CHARACTERISTICS CURVES** ( $T_A = 25\text{ }^{\circ}\text{C}$  unless otherwise noted)

Fig. 1 - Forward Current Derating Curve

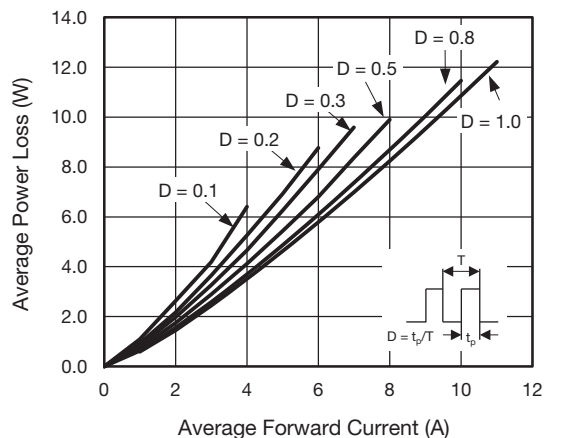


Fig. 2 - Forward Power Loss Characteristics Per Diode

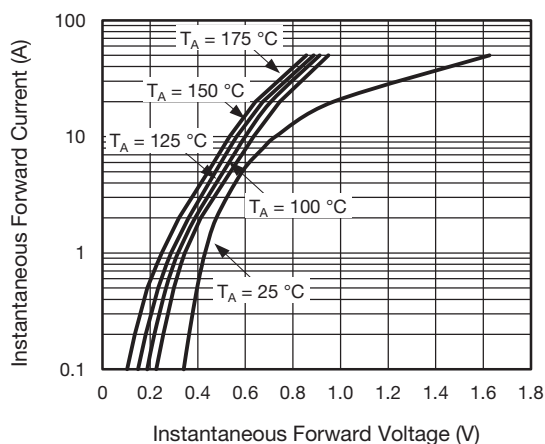


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

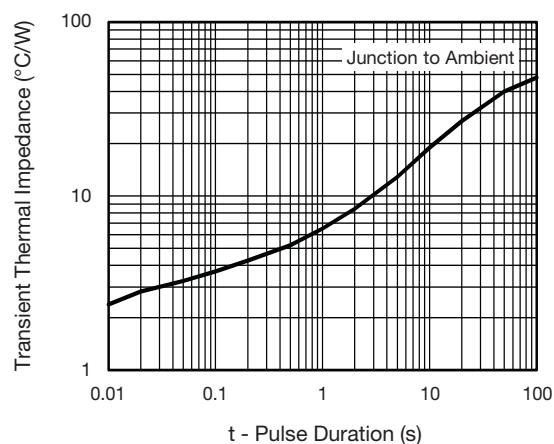


Fig. 6 - Typical Transient Thermal Impedance Per Device

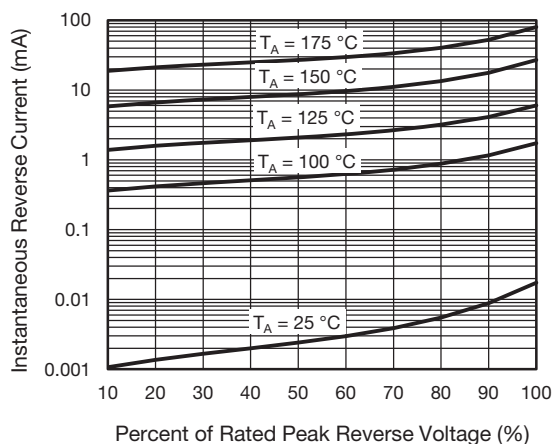


Fig. 4 - Typical Reverse Characteristics Per Diode

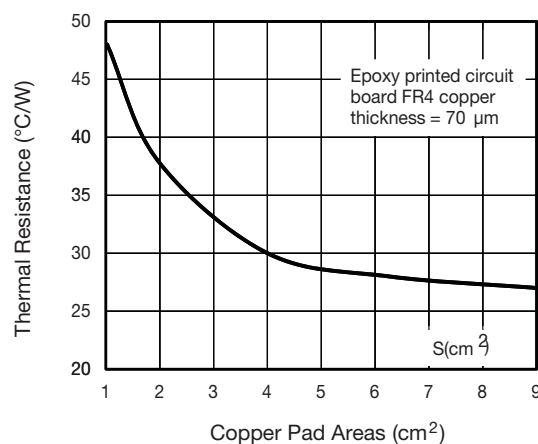


Fig. 7 - Thermal Resistance Junction-to-Ambient vs. Copper Pad Areas

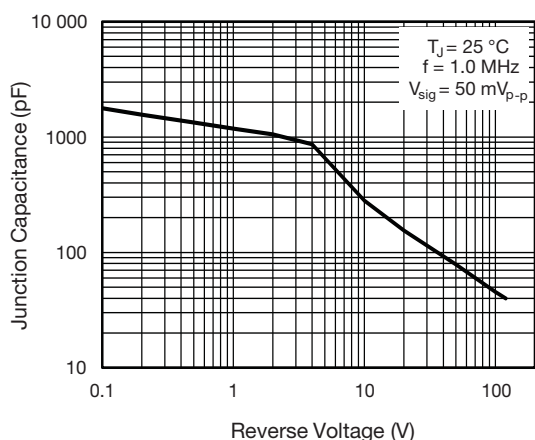
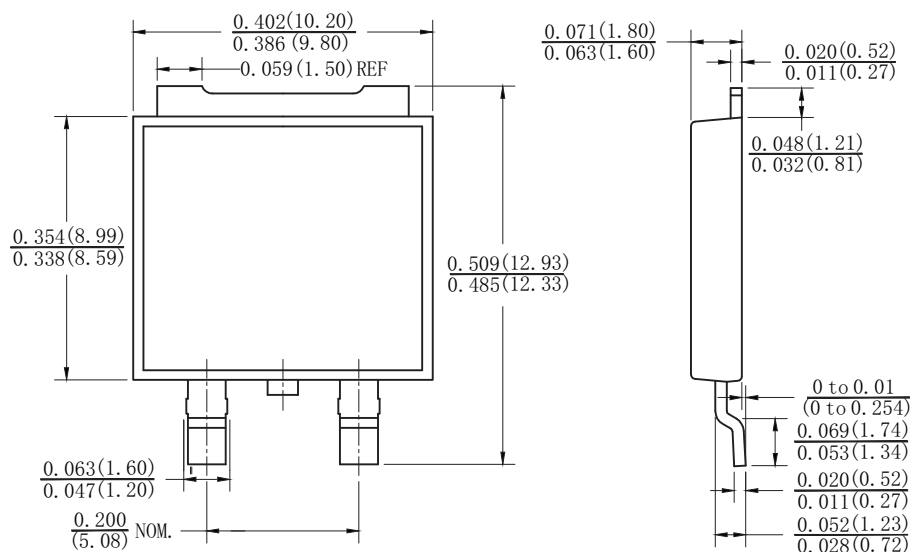


Fig. 5 - Typical Junction Capacitance Per Diode

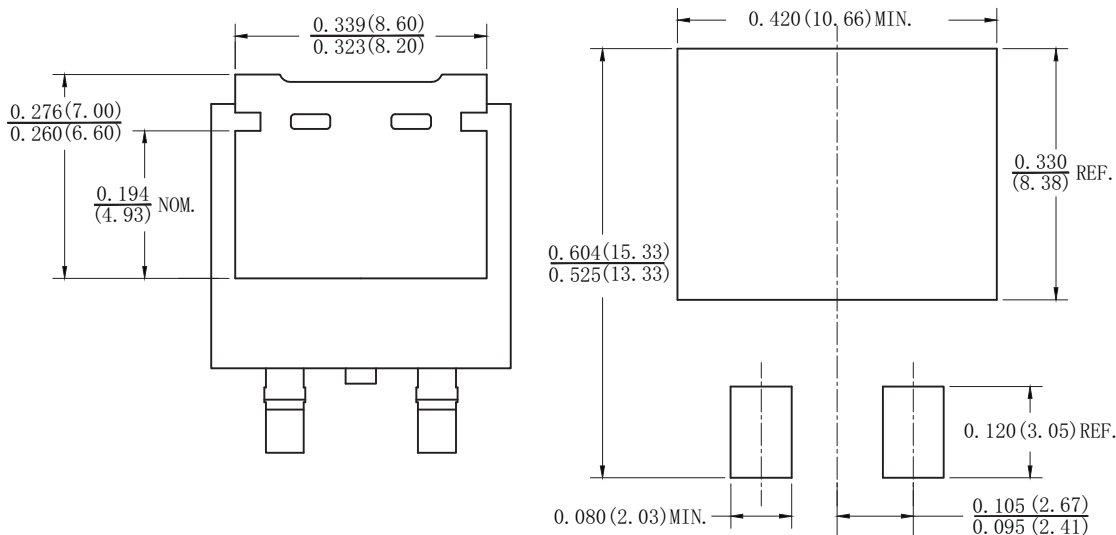


## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

### TO-263AC (SMPD)



### Mounting Pad Layout





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